



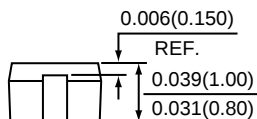
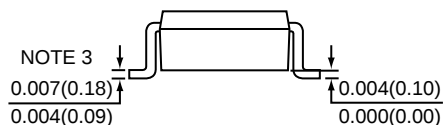
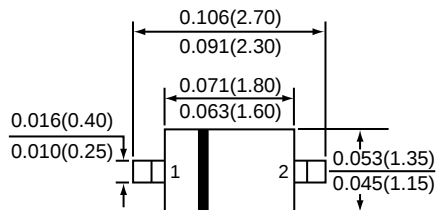
MMDL914T1

SURFACE MOUNT HIGH-SPEED SWITCHING DIODE

Reverse Breakdown Voltage - 100 Volts

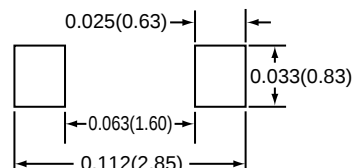
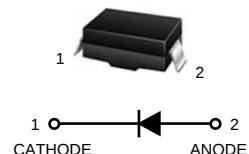
Peak Forward Current - 200mA

SOD-323



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.

*Dimensions in inches and (millimeters)



Device Marking : MMDL6050T1 = 5A

MAXIMUM RATINGS

Ratings at 25 °C ambient temperature unless otherwise specified.			
	SYMBOLS	VALUE	UNITS
Continuous Reverse Voltage	V_R	100	Vdc
Peak Forward Current	I_F	200	mAdc
Peak Forward Surge Current	I_{FSM}	500	mAdc

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOLS	MAX.	UNITS
Total Device Dissipation FR-5 Board, $T_A=25^{\circ}\text{C}$ Derate above 25°C	P_D	200 1.57	mW mW / °C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	°C / W
Junction and Storage Temperature	T_J, T_{STG}	150	°C

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

CHARACTERISTIC		SYMBOLS	MIN.	MAX.	UNITS
Reverse Breakdown Voltage	($I_{BR}=100\mu\text{A}$)	$V_{(BR)}$	100	-	Vdc
Reverse Voltage Leakage Current	($V_R=20\text{Vdc}$) ($V_R=75\text{Vdc}$)	I_R	- -	25 5.0	nAdc uAdc
Forward Voltage	($I_F=10\text{mAdc}$)	V_F	-	1.0	Vdc
Junction Capacitance	($V_R=0\text{V}$, $f = 1.0\text{MHz}$)	C_J	-	4.0	pF
Reverse Recovery Time	($I_F=I_R=10\text{mAdc}$, $I_R(\text{REC}) = 1.0\text{mAdc}$)	t_{rr}	-	4.0	nS

RATINGS AND CHARACTERISTIC CURVES OF MMDL914T1

FIGURE 1. RECOVERY TIME EQUIVALENT TEST CIRCUIT

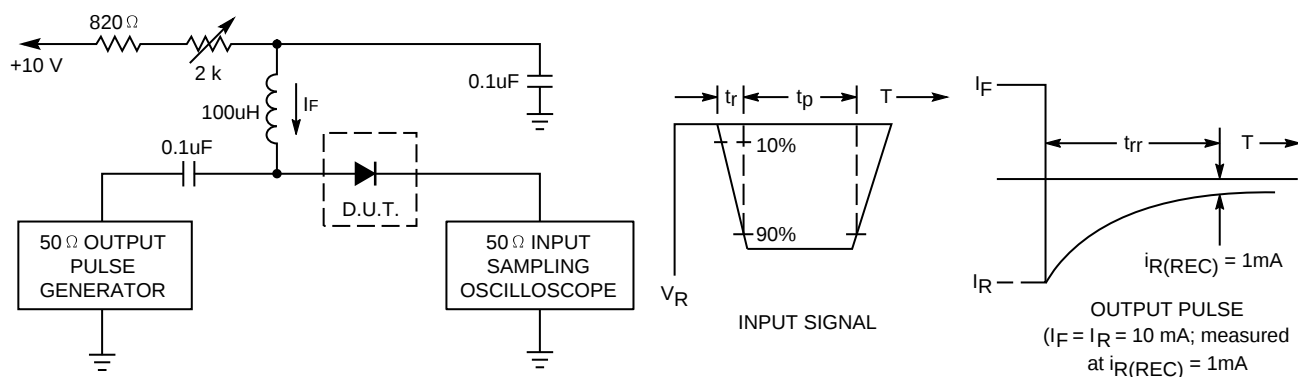


FIGURE 2. FORWARD VOLTAGE

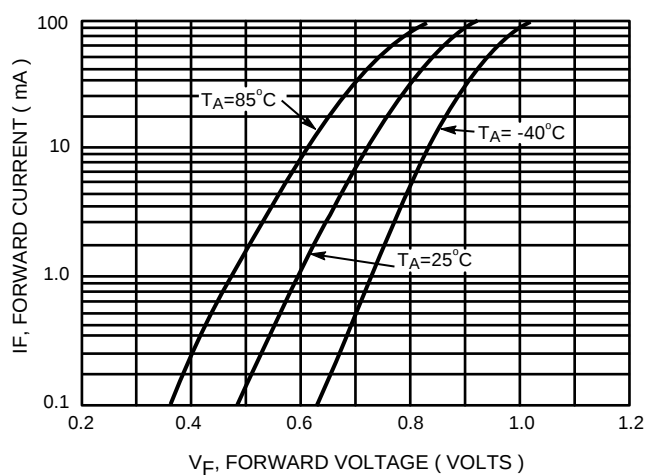


FIGURE 3. LEAKAGE CURRENT

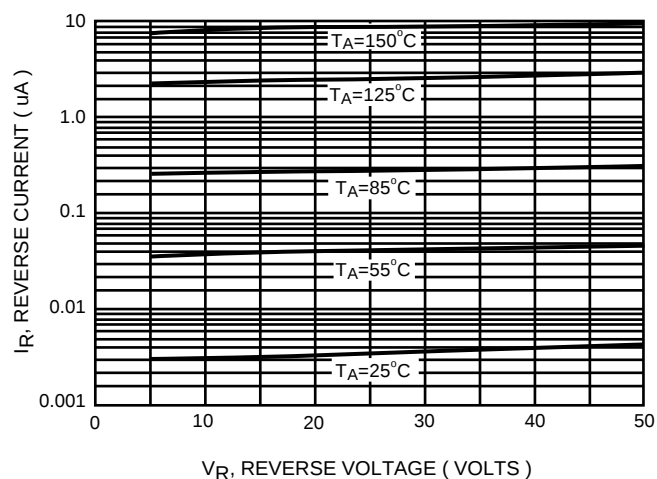


FIGURE 4. CAPACITANCE

